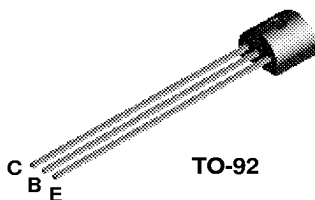


MPS6562



PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 500 mA. Sourced from Process 67. See TN4033A for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	25	V
V _{CBO}	Collector-Base Voltage	25	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	1.0	A
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		MPS6562	
P _D	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	83.3	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	200	°C/W

PNP General Purpose Amplifier

(continued)

Electrical Characteristics

TA = 25 °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 10 \text{ mA}, I_B = 0$	25		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100 \text{ } \mu\text{A}, I_E = 0$	25		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 100 \text{ } \mu\text{A}, I_C = 0$	5.0		V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 20 \text{ V}, I_E = 0$		100	nA
I_{CEO}	Collector Cutoff Current	$V_{CE} = 25 \text{ V}, I_E = 0$		100	nA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 4.0 \text{ V}, I_C = 0$		100	nA

ON CHARACTERISTICS*

h_{FE}	DC Current Gain	$V_{CE} = 1.0 \text{ V}, I_C = 10 \text{ mA}$ $V_{CE} = 1.0 \text{ V}, I_C = 100 \text{ mA}$ $V_{CE} = 1.0 \text{ V}, I_C = 500 \text{ mA}$	35 50 50	200	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE} = 1.0 \text{ V}, I_C = 500 \text{ mA}$		1.2	V

SMALL SIGNAL CHARACTERISTICS

C_{ob}	Output Capacitance	$V_{CB} = 10 \text{ V}, f = 100 \text{ kHz}$		30	pF
f_T	Current Gain - Bandwidth product	$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 20 \text{ MHz}$	60		MHz

*Pulse Test: Pulse Width $\leq 300 \text{ } \mu\text{s}$, Duty Cycle $\leq 2.0\%$